

PMEG2010AEK 1 A very low V_F MEGA Schottky barrier rectifierRev. 01 — 30 March 2007Pr

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT346 (SC-59A/TO-236) small Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Forward current: $I_F \le 1 A$
- Reverse voltage: V_R ≤ 20 V
- Very low forward voltage
- Small SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current	$T_{sp} \le 55 \ ^{\circ}C$	-	-	1	А
V _R	reverse voltage		-	-	20	V
V _F	forward voltage	I _F = 1 A	<u>[1]</u> _	400	450	mV



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2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Symbol
1	anode	_	
2	not connected		3
3	cathode	1 2	1 2 n.c. 006aaa436

3. Ordering information

Table 3. Orderin	ig informatio	n	
Type number	Package		
	Name	Description	Version
PMEG2010AEK	SC-59A	plastic surface-mounted package; 3 leads	SOT346

4. Marking

Table 4.	Marking codes	
Type num	ber	Marking code
PMEG201	0AEK	H1

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0 7 (,		
Symbol	Parameter	Conditions	Min	Max	Unit
V _R	reverse voltage		-	20	V
I _F	forward current	$T_{sp} \le 55 \ ^{\circ}C$	-	1	А
I _{FRM}	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$	-	3	А
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	-	4.5	А
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
			[2] _	350	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

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6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
			[2]	-	500	K/W
			[3]	-	360	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[4]</u> _	-	150	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Soldering point of cathode tab.

7. Characteristics

Table 7.Characteristics

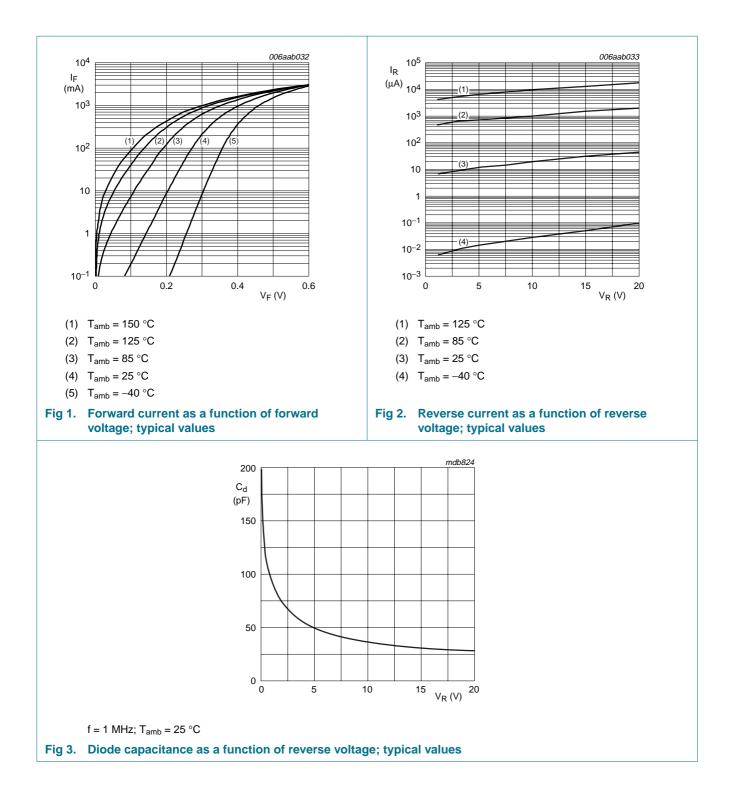
 $T_{amb} = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F fo	forward voltage		<u>[1]</u>			
		I _F = 10 mA	-	200	220	mV
		I _F = 100 mA	-	265	290	mV
		I _F = 1 A	-	400	450	mV
I _R reve	reverse current	V _R = 5 V	-	15	20	μΑ
		V _R = 10 V	-	20	80	μΑ
		V _R = 20 V	-	50	200	μA
C _d	diode capacitance	V _R = 5 V; f = 1 MHz	-	55	70	pF

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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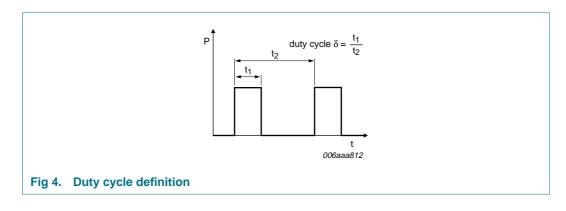
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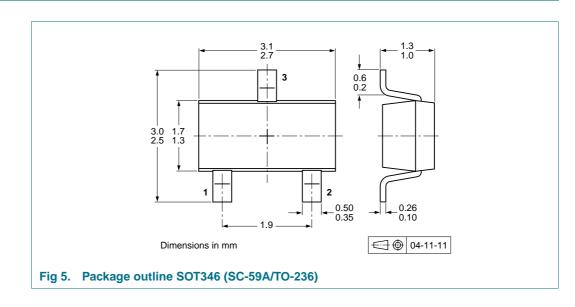
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8. Test information



9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity	
			3000	10000	
PMEG2010AEK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-135	

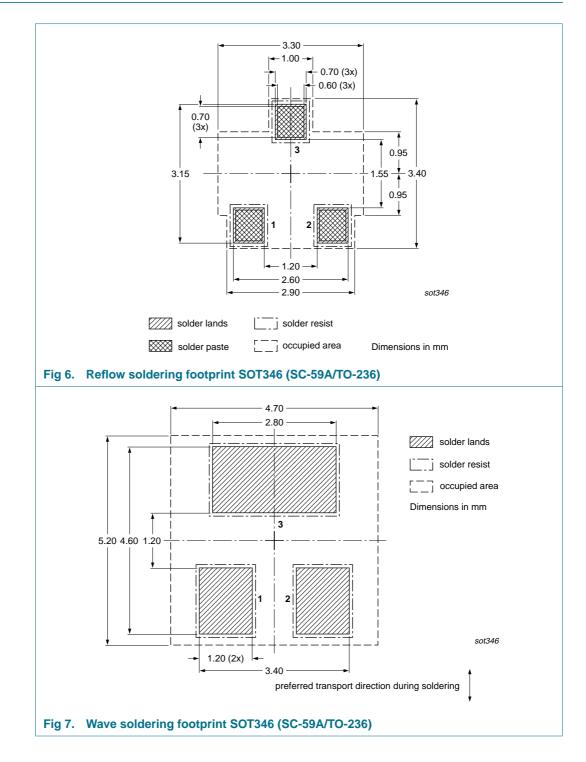
[1] For further information and the availability of packing methods, see <u>Section 14</u>.

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11. Soldering



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12. Revision history

Table 9. Revision his	Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PMEG2010AEK_1	20070330	Product data sheet	-	-		

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13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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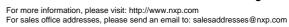
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